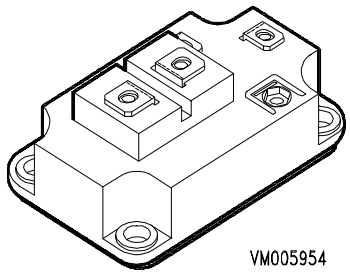
IGBT Power Module

- Single switch
- Including fast free-wheeling diodes
- Package with insulated metal base plate



Type	V_{CE}	I_C	Package	Ordering Code
BSM 300 GA 120 DN2	1200V	430A	SINGLE SWITCH 1	C67076-A2007-A70
BSM 300 GA 120 DN2 S	1200V	430A	SSW SENSE 1	C67070-A2017-A70

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1200	V
Collector-gate voltage	V_{CGR}		
R_{GE} = 20 kΩ		1200	
Gate-emitter voltage	V_{GE}	± 20	
DC collector current	I_C		A
T_C = 25 °C		430	
T_C = 80 °C		300	
Pulsed collector current, t_p = 1 ms	I_{Cpuls}		
T_C = 25 °C		860	
T_C = 80 °C		600	
Power dissipation per IGBT	P_{tot}		W
T_C = 25 °C		2500	
Chip temperature	T_j	+ 150	°C
Storage temperature	T_{stg}	-40 ... + 125	
Thermal resistance, chip case	R_{thJC}	≤ 0.05	K/W
Diode thermal resistance, chip case	R_{thJCD}	≤ 0.125	
Insulation test voltage, t = 1min.	V_{is}	2500	Vac
Creepage distance	-	20	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	sec
IEC climatic category, DIN IEC 68-1	-	40 / 125 / 56	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Gate threshold voltage $V_{GE} = V_{CE}$, I_C = 12 mA	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage V_{GE} = 15 V, I_C = 300 A, T_j = 25 °C V_{GE} = 15 V, I_C = 300 A, T_j = 125 °C	$V_{CE(sat)}$	 - -	 2.5 3.1	 3 3.7	
Zero gate voltage collector current V_{CE} = 1200 V, V_{GE} = 0 V, T_j = 25 °C V_{CE} = 1200 V, V_{GE} = 0 V, T_j = 125 °C	I_{CES}	 - -	 4 16	 5.6 -	mA
Gate-emitter leakage current V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	 -	 -	 320	nA
AC Characteristics					
Transconductance V_{CE} = 20 V, I_C = 300 A	g_{fs}	 124	 -	 -	S
Input capacitance V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz	C_{iss}	 -	 22	 -	nF
Output capacitance V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz	C_{oss}	 -	 3.3	 -	
Reverse transfer capacitance V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz	C_{rss}	 -	 1.2	 -	

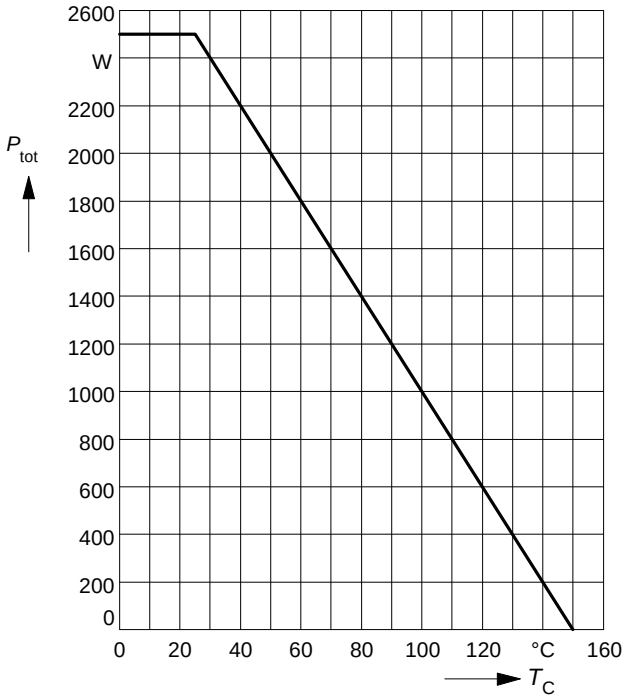
Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Switching Characteristics, Inductive Load at T_j = 125 °C					
Turn-on delay time V_{CC} = 600 V, V_{GE} = 15 V, I_C = 300 A R_{Gon} = 3.3 Ω	$t_{d(on)}$	- -	100 -	200 -	ns
Rise time V_{CC} = 600 V, V_{GE} = 15 V, I_C = 300 A R_{Gon} = 3.3 Ω	t_r	- -	110 -	220 -	
Turn-off delay time V_{CC} = 600 V, V_{GE} = -15 V, I_C = 300 A R_{Goff} = 3.3 Ω	$t_{d(off)}$	- -	600 -	800 -	
Fall time V_{CC} = 600 V, V_{GE} = -15 V, I_C = 300 A R_{Goff} = 3.3 Ω	t_f	- -	80 -	120 -	
Free-Wheel Diode					
Diode forward voltage I_F = 300 A, V_{GE} = 0 V, T_j = 25 °C I_F = 300 A, V_{GE} = 0 V, T_j = 125 °C	V_F	- -	2.3 1.8	2.8 -	V
Reverse recovery time I_F = 300 A, V_R = -600 V, V_{GE} = 0 V di_F/dt = -2500 A/µs, T_j = 125 °C	t_{rr}	-	0.55	-	µs
Reverse recovery charge I_F = 300 A, V_R = -600 V, V_{GE} = 0 V di_F/dt = -2500 A/µs T_j = 25 °C T_j = 125 °C	Q_{rr}	- -	14 40	- -	µC

Power dissipation

$P_{tot} = f(T_C)$

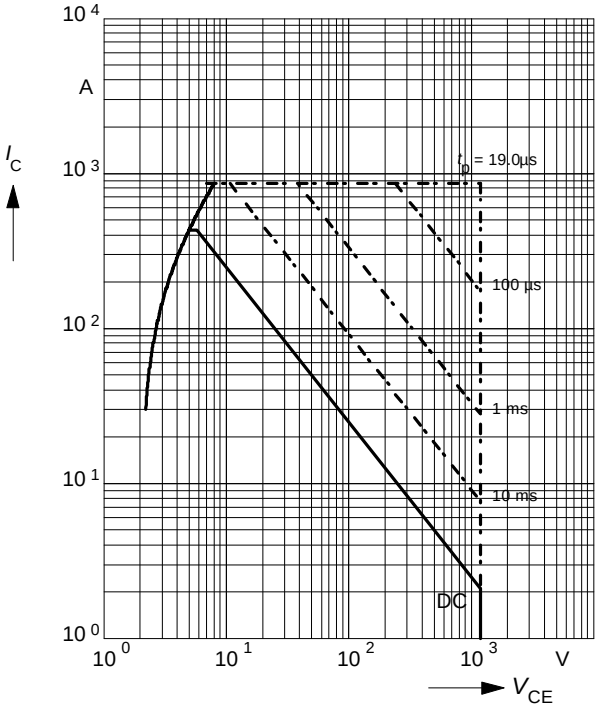
parameter: $T_j \leq 150$ °C



Safe operating area

$I_C = f(V_{CE})$

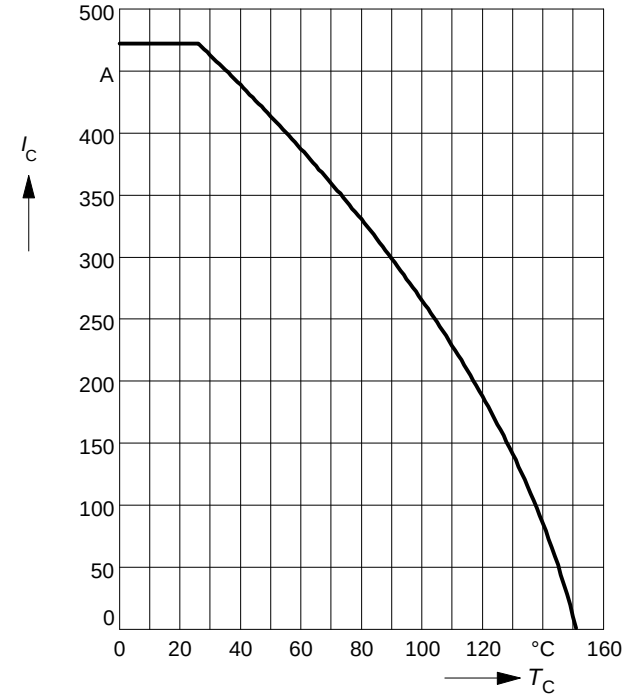
parameter: $D = 0$, $T_C = 25$°C , $T_j \leq 150$ °C



Collector current

$I_C = f(T_C)$

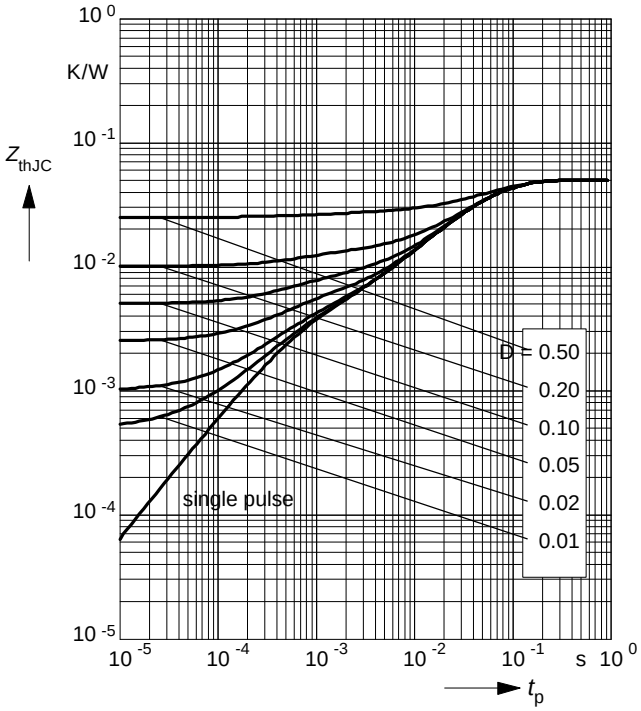
parameter: $V_{GE} \geq 15$ V , $T_j \leq 150$ °C



Transient thermal impedance IGBT

$Z_{th\,JC} = f(t_p)$

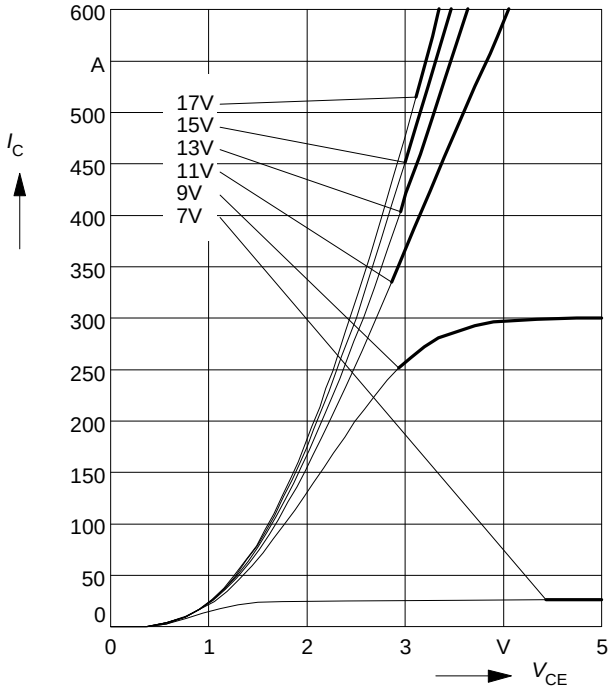
parameter: $D = t_p / T$



Typ. output characteristics

$I_C = f(V_{CE})$

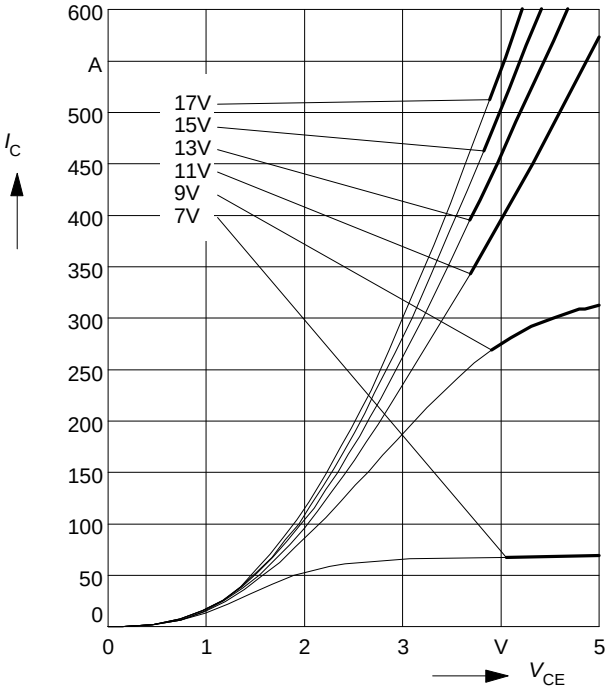
parameter: t_p = 80 µs, T_j = 25 °C



Typ. output characteristics

$I_C = f(V_{CE})$

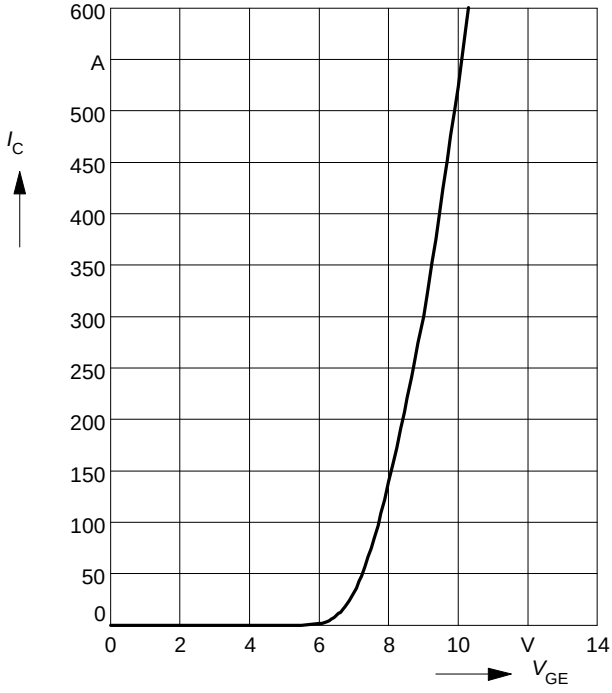
parameter: t_p = 80 µs, T_j = 125 °C



Typ. transfer characteristics

$I_C = f(V_{GE})$

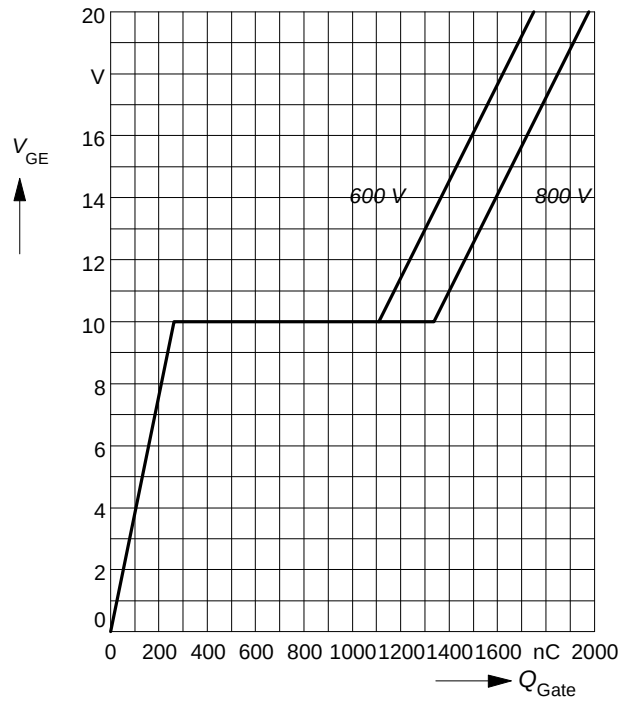
parameter: t_p = 80 µs, V_{CE} = 20 V



Typ. gate charge

$V_{GE} = f(Q_{Gate})$

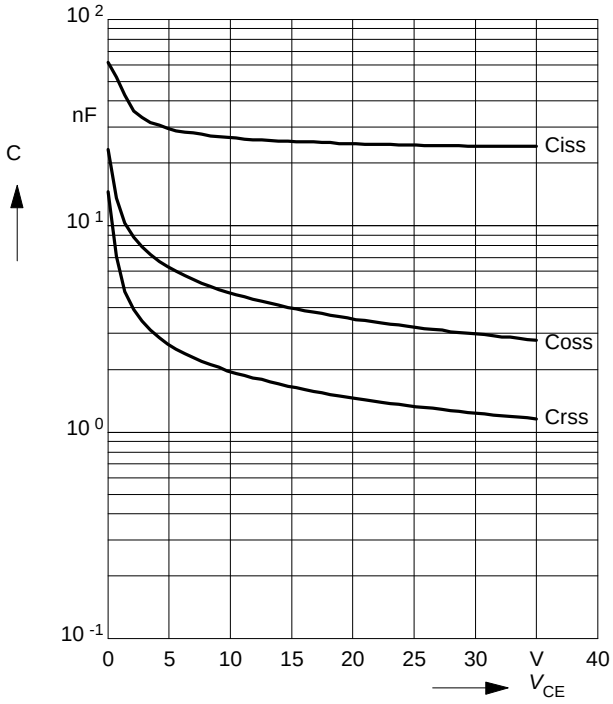
parameter: $I_{C\ puls}$ = 300 A



Typ. capacitances

$C = f(V_{CE})$

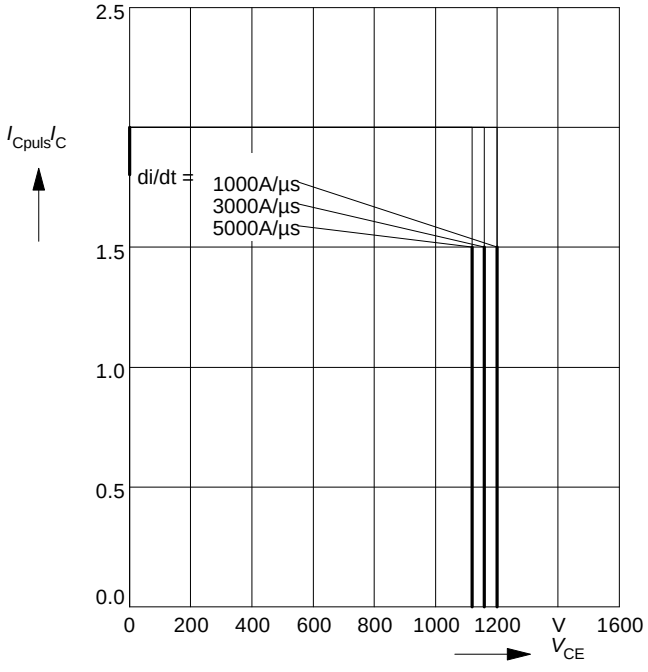
parameter: V_{GE} = 0 V, f = 1 MHz



Reverse biased safe operating area

$I_{Cpuls} = f(V_{CE})$, T_j = 150°C

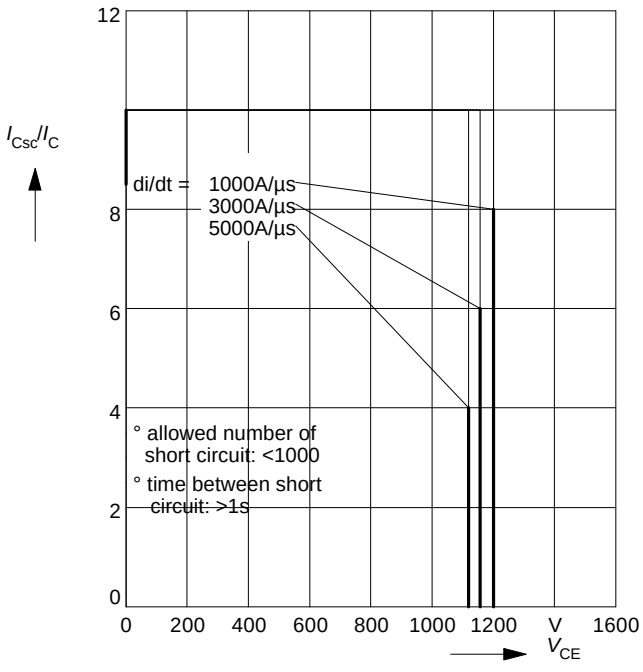
parameter: V_{GE} = ± 15 V, $t_p \leq$ 1 ms, L < 20 nH



Short circuit safe operating area

$I_{Csc} = f(V_{CE})$, T_j = 150°C

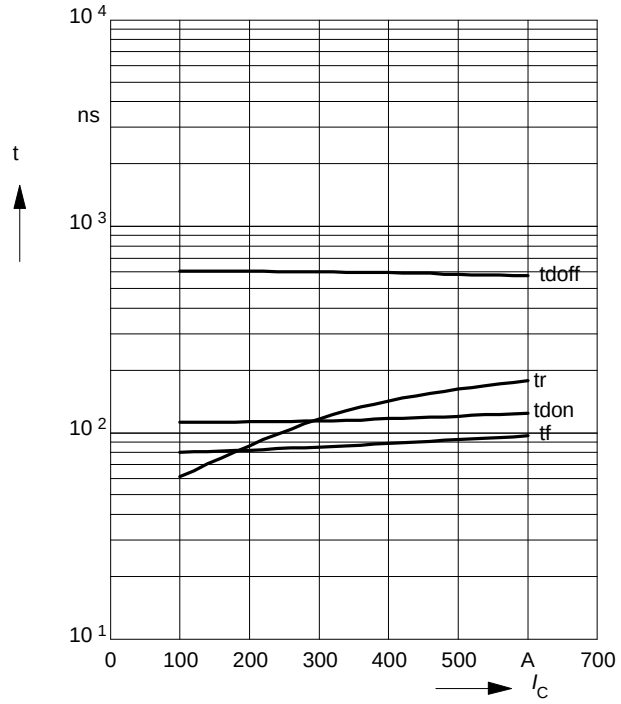
parameter: V_{GE} = ± 15 V, $t_{SC} \leq$ 10 µs, L < 20 nH



Typ. switching time

$I = f(I_C)$, inductive load , T_j = 125°C

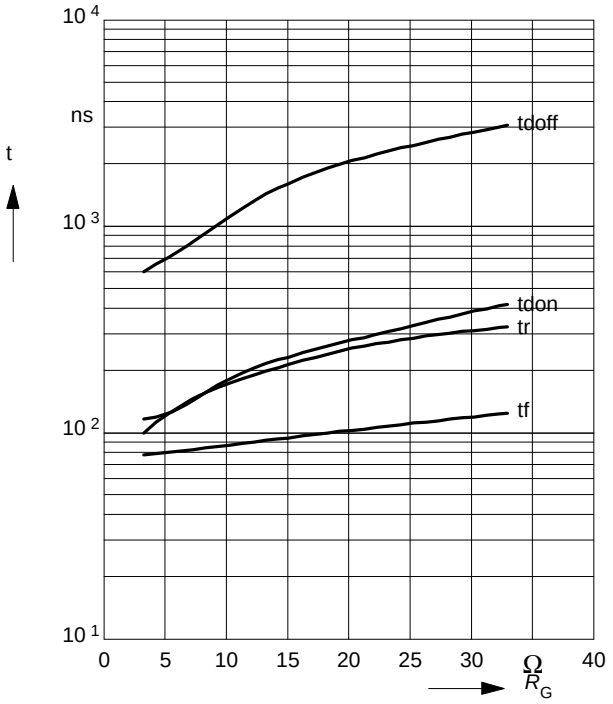
par.: V_{CE} = 600 V, V_{GE} = ± 15 V, R_G = 3.3 Ω



Typ. switching time

$t = f(R_G)$, inductive load , T_j = 125°C

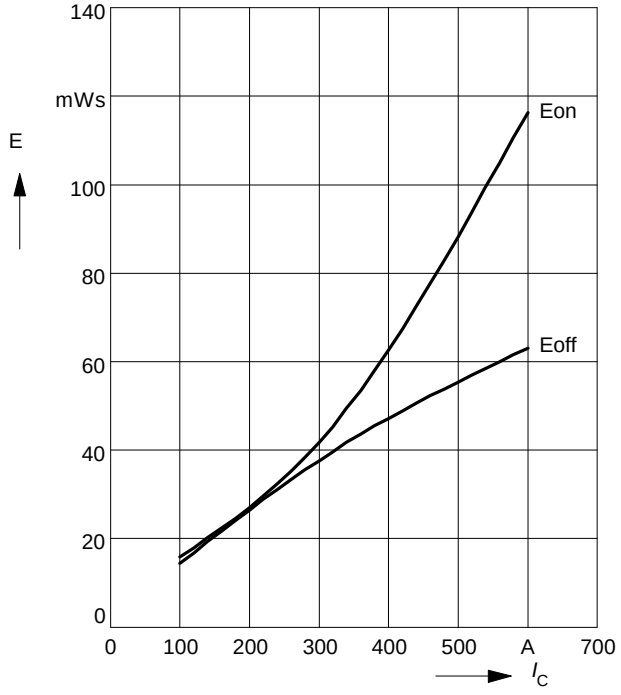
par.: V_{CE} = 600 V, V_{GE} = ± 15 V, I_C = 300 A



Typ. switching losses

$E = f(I_C)$, inductive load , T_j = 125°C

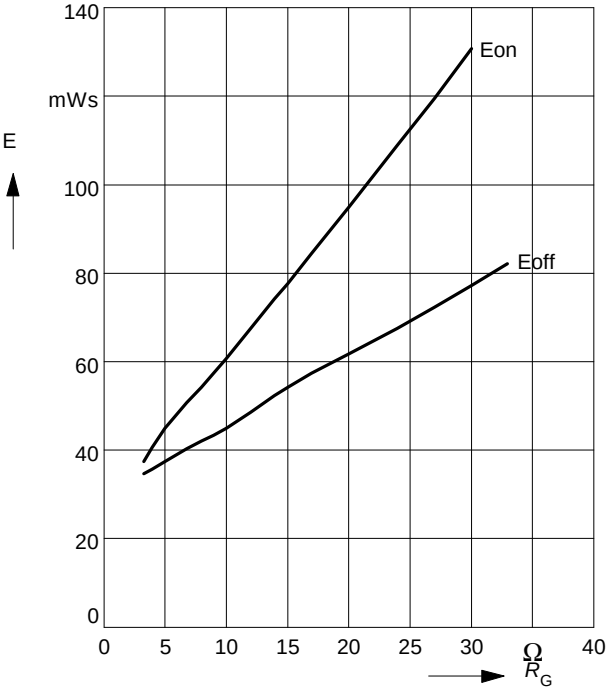
par.: V_{CE} = 600 V, V_{GE} = ± 15 V, R_G = 3.3 Ω



Typ. switching losses

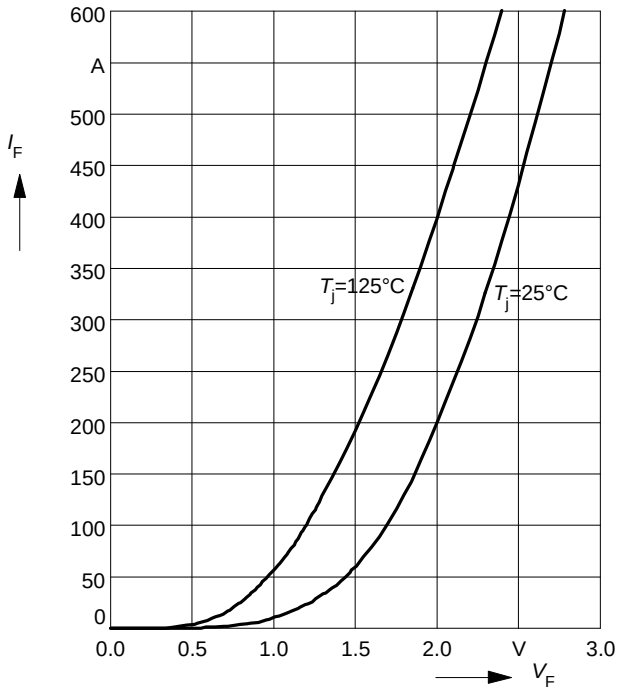
$E = f(R_G)$, inductive load , T_j = 125°C

par.: V_{CE} = 600V, V_{GE} = ± 15 V, I_C = 300 A



Forward characteristics of fast recovery reverse diode $I_F = f(V_F)$

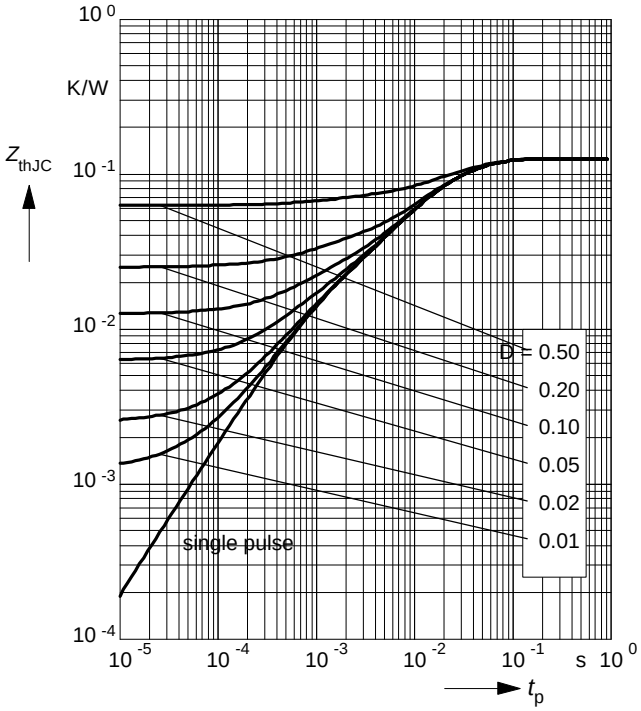
parameter: T_j



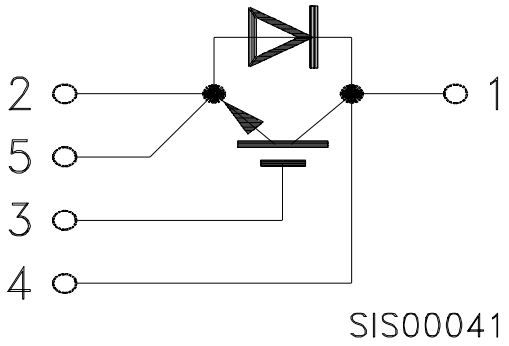
Transient thermal impedance Diode

$Z_{th\,JC} = f(t_p)$

parameter: $D = t_p / T$



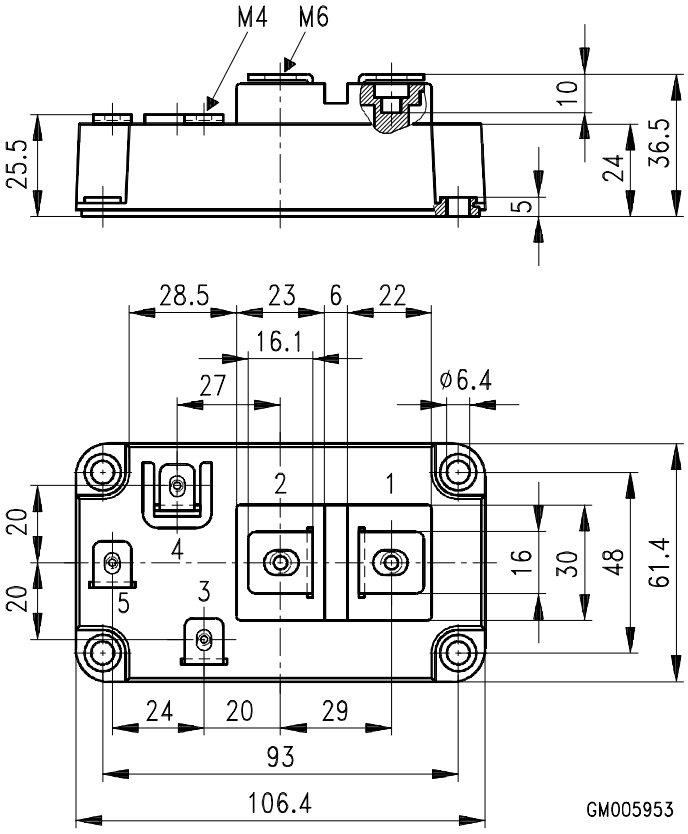
Circuit Diagram



Package Outlines

Dimensions in mm

Weight: 420 g

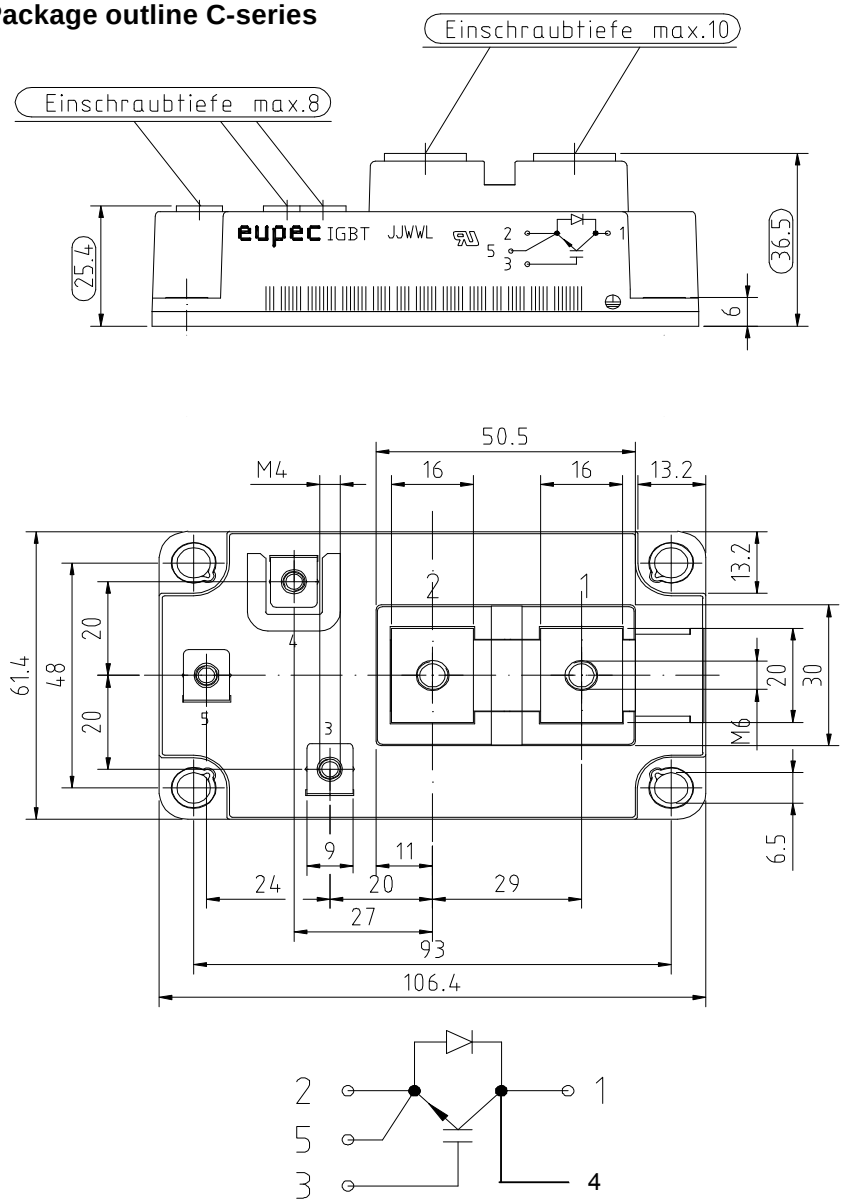


Anhang C-Serie
Appendix C-series

Gehäuse spezifische Werte
Housing specific values

			typ.	
Modulinduktivität stray inductance module		L_{sCE}	20	nH

Gehäusemaße C-Serie
Package outline C-series



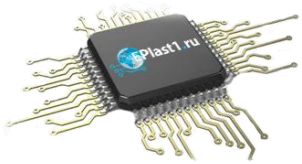
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.